ERRATA

Erratum to: Characteristics of Schottky Rectifier Diodes Based on Silicon Carbide at Elevated Temperatures

A. M. Strel'chuk^{a,*}, A. A. Lebedev^a, and P. V. Bulat^b

^a *Ioffe Institute, St. Petersburg, 194021 Russia*

^b *Baltic State Technical University, St. Petersburg, 190005 Russia*

^{*}*e-mail: anatoly.strelchuk@mail.ioffe.ru*

Received July 23, 2020; revised July 27, 2020; accepted July 27, 2020

DOI: 10.1134/S1063782621030192

1. Affiliations of authors A. M. Strel'chuk^{a,*}, A. A. Lebedev^{a,b}, and P. V. Bulat^b should read as follows:

^a*Ioffe Institute, St. Petersburg, 194021 Russia*

^b*Baltic State Technical University, St. Petersburg, 190005 Russia*

2. Section ACKNOWLEDGMENTS should read as follows:

FUNDING

This work was financially supported by the Ministry of Science and Higher Education of Russian Fed-

eration during the implementation of the project “Creating a leading scientific and technical reserve in the development of advanced technologies for small gas turbine, rocket and combined engines of ultra-light launch vehicles, small spacecraft and unmanned aerial vehicles that provide priority positions for Russian companies in emerging global markets of the future”, no. FZWF-2020-0015.

The original article can be found online at <https://doi.org/10.1134/S1063782620120374>